**Product data sheet** 

## 1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 2. Features and benefits

- · High blocking voltage capability
- Low holding current for low current loads and lowest EMI at commutation
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Direct triggering from low power drivers and logic ICs
- Sensitive gate

### 3. Applications

- General purpose motor control
- · General purpose switching

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	rameter Conditions					Unit
Absolute	maximum rating						
$V_{DRM}$	repetitive peak off-state voltage			6	000		V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \le 107 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	4			А	
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 20 \text{ms}$ ; Fig. 4; Fig. 5; Fig. 3	25			Α	
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static ch	aracteristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	2.5	10	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_i = 25 \text{ °C; } Fig. 7$			-	4	10	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-;}$ $T_i = 25 ^{\circ}\text{C; } \frac{\text{Fig. } 7}{\text{C}}$		-	5	10	mA	
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	11	25	mA
I <sub>H</sub>	holding current $V_D = 12 \text{ V; } T_j = 25 \text{ °C; } Fig. 9$			-	2.2	15	mA

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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		N
3	G	gate		T2 T1
mb	T2	mounting base; main terminal 2		sym051

## 6. Ordering information

### **Table 3. Ordering information**

Type number	Package			
	Name	Description	Version	
BT136-600E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78	

## 7. Marking

#### Table 4. Marking codes

Type number	Marking codes
BT136-600E	BT136-600E

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 107 °C; <u>Fig 1</u> ; <u>Fig 2</u> ; <u>Fig 3</u>	4	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25  ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; Fig 4; Fig 5; Fig 3	25	А
		full sine wave; $T_{j(init)} = 25  ^{\circ}\text{C}$ ; $t_p = 16.7  \text{ms}$ ; Fig 4; Fig 5;	27	А
l²t	I <sup>2</sup> t for fusing	$t_p$ = 10 ms; SIN	3.1	A <sup>2</sup> s
dl <sub>⊤</sub> /dt		I <sub>G</sub> = 20 mA; T2+ G+	50	A/µs
	current	I <sub>G</sub> = 20 mA; T2+ G-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G-	50	A/µs
		I <sub>G</sub> = 50 mA; T2- G+	10	A/µs
I <sub>GM</sub>	peak gate current		2	Α
$P_{\text{GM}}$	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		125	°C

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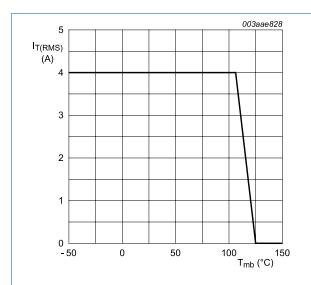
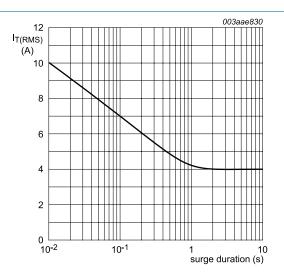
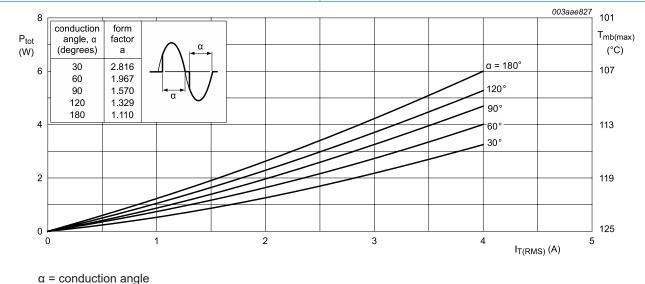


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz;  $T_{mb} \le 107$  °C Fig. 2. RMS on-state current as a function of surge duration; maximum values



 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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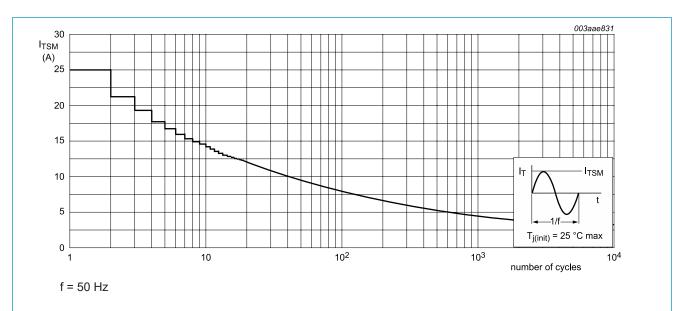
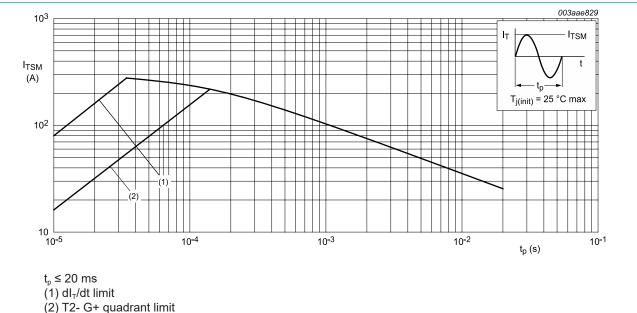


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



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### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance	full cycle; Fig 6		-	-	3	K/W
from junction to mounting base		half cycle; <u>Fig 6</u>		-	-	3.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		-	60	-	K/W

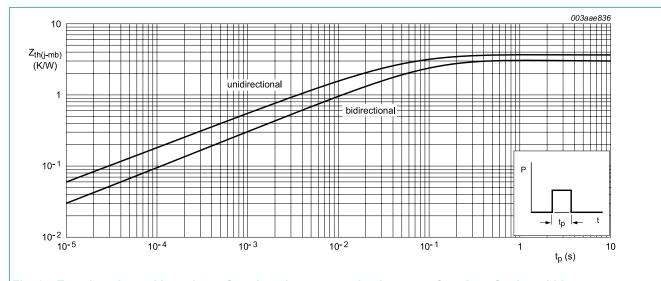


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

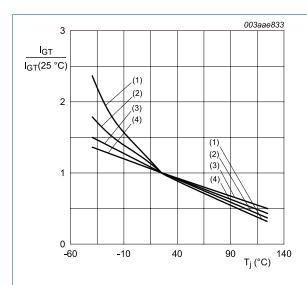
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## 10. Characteristics

#### **Table 7. Characteristics**

<b>Symbol</b>	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
I <sub>GT</sub> gate trigger current		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	4	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	11	25	mA
l <sub>L</sub>	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	3	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 8$	-	10	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	2.5	15	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	4	20	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	2.2	15	mA
V <sub>T</sub>	on-state voltage	I <sub>τ</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.4	1.7	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
$I_D$	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit		50	-	V/µs
<b>t</b> <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 6 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

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(1) T2- G+

(2) T2- G-

(3) T2+ G-

-60

-10

junction temperature

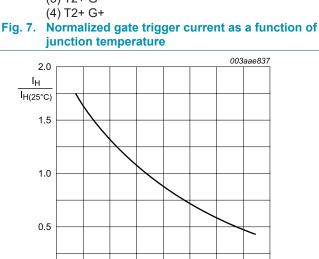


Fig. 9. Normalized holding current as a function of junction temperature

T<sub>j</sub> (°C)

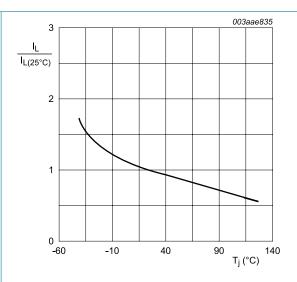
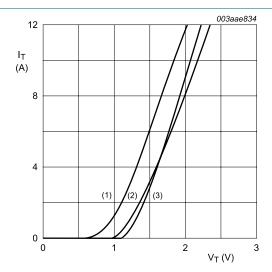


Fig. 8. Normalized latching current as a function of junction temperature



 $V_o = 1.27 \text{ V}; R_s = 0.091 \Omega$ 

(1)  $T_j = 125$  °C; typical values (2)  $T_j = 125$  °C; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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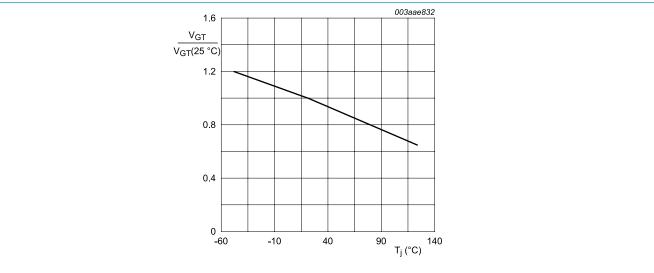
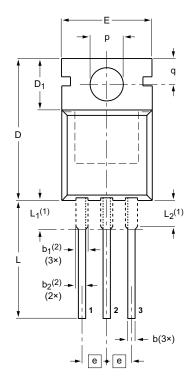


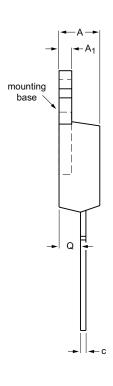
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 





0 5 10 mm

#### **DIMENSIONS** (mm are the original dimensions)

UNIT	Α	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13	

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### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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